

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to : Commissioner of Patents and Trademarks, Washington, D.C. 20231, on October 3, 2003. The applicant and/or attorney requests the date of deposit as the filing date. Depositor: Karen Cinq-Mars

Karen Cinq-Mars 10/3/03  
(Signature & date)



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Filed application of : October 3, 2003  
Bruley, et al. : Group Art Unit:  
Serial No. 10/605,128 : Examiner:  
Filed: 9/10/2003 : International Business Machines Corporation  
2070 Route 52  
Hopewell Junction, NY 12533

**TITLE:** CAPACITOR AND FABRICATION METHOD USING ULTRA-HIGH VACUUM CVD OF SILICON

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

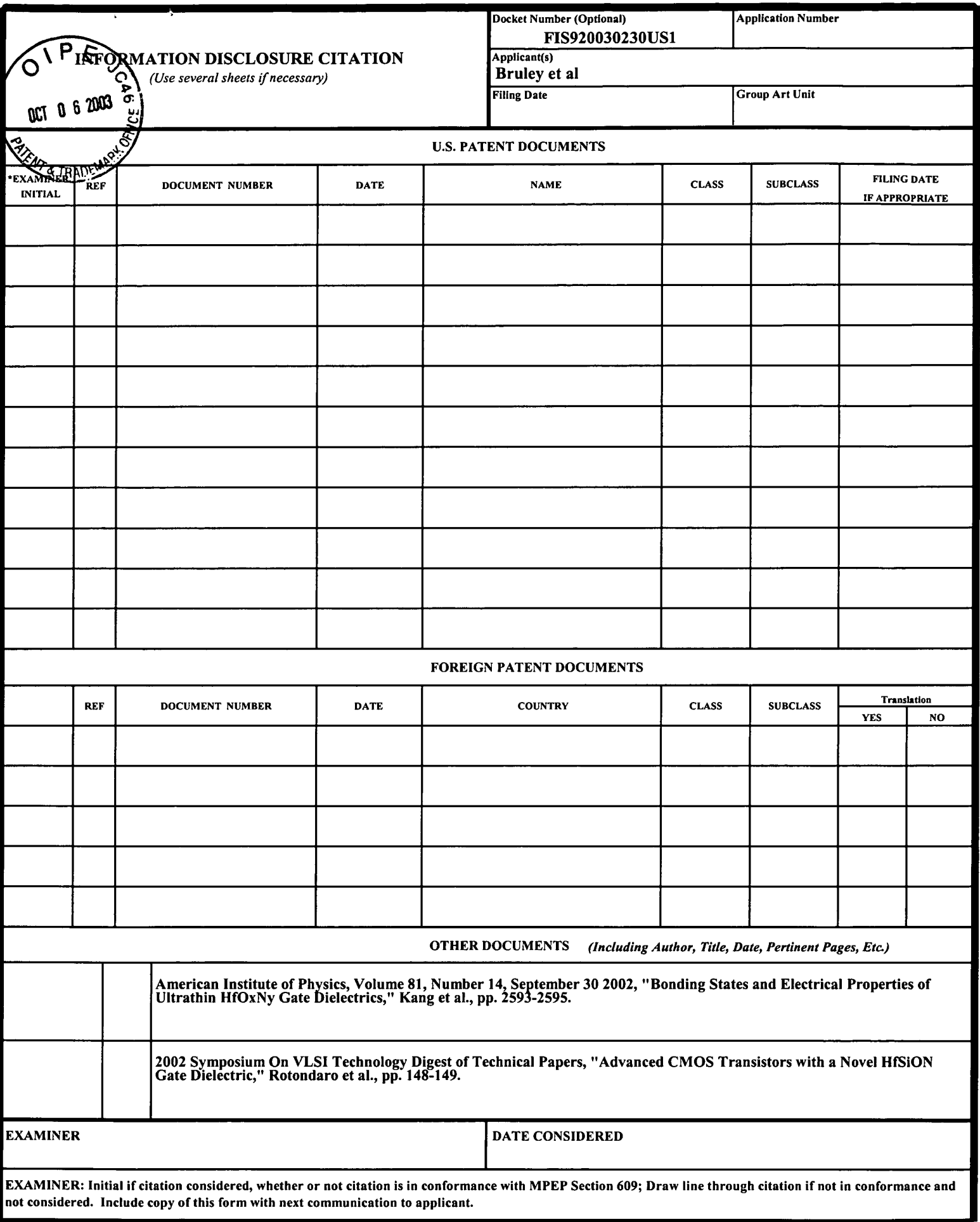
Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,  
Bruley, et al.

By Margaret A. Pepper  
Margaret A. Pepper  
Registration No. 45,008  
Telephone No. 845-894-4713



# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

FIS920030230US1

Application Number

Applicant(s)

Bruley et al

Filing Date

Group Art Unit

\*EXAMINER  
INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

2002 American Institute of Physics, Volume 80, Number 17, April 29, 2002, "Application of HfSiON as a Gate Dielectric Material," Visokay et al., pp. 3183-3185.

Journal of the Korean Physical Society, Volume 37, Number 6, December 2000, "Electrical Characteristics of AlOxNy Prepared by Oxidation of Sub-10-nm-thick AlN Films for MOS Gate Dielectric Applications," Jeon et al., pp. 886-888.

IEEE PUBADDR, Piscataway, NJ, 1998 International Conference on Ion Implantation Technology, Ion Implantation Technology, Volume 2, June 1998, "Silicon-Aluminum Oxynitride Composite Films Deposited by Reactive Ion Beam Sputtering," Ogawa et al., pp. 775-778.

2002 American Institute of Physics, Volume 80, Number 17, April 29, 2002, "Suppressed Boron Penetration in p+ polycrystalline-Si/Al2O3/Si Metal-Oxide-Semiconductor Structures," Cho, et al., pp. 3177-3179.

2002 American Institute of Physics, Volume 80, Number 18, May 6, 2002, "Excellent Thermal Stability of Al2O3 Stack Structure for Metal-Oxide-Semiconductor Gate Dielectrics Application," Chang et al., pp.3385-3387.

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.